

#### DIRECT QUADRATURE MODULATOR

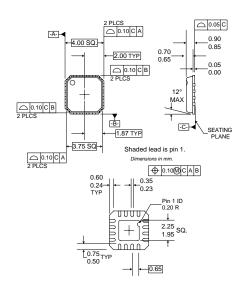
#### RoHS Compliant & Pb-Free Product

#### Typical Applications

- UMTS Base Stations
- CDMA Base Stations
- GSM-EDGE/EGSM Base Stations
- WLAN and WLL Systems
- GMSK, QPSK, DQPSK, QAM Modulation

#### **Product Description**

The RF2850 is a direct quadrature modulator for use in base stations and other communications systems. RF2850 supports PCS, GSM, EDGE, CDMA2000, and UMTS standards. This device features a narrow-band operation at 1700MHz to 2500MHz with excellent carrier and sideband suppression and ultra low noise floor. The device is manufactured on an advanced GaAs HBT process. The RF2850 operates from a single 5V supply and is packaged in a low cost 4mmx4mm 16-pin leadless package.

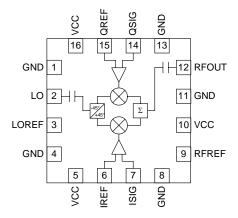


Package Style: QFN, 16-Pin, 4x4

#### Optimum Technology Matching® Applied

- ☐ Si BJT Si Bi-CMOS
- **▼** GaAs HBT ☐ SiGe HBT
- GaAs MESFET ☐ Si CMOS

- InGaP/HBT
- GaN HEMT SiGe Bi-CMOS



**Functional Block Diagram** 

#### **Features**

- Typical Carrier Suppression>40dBc
- Typical Sideband Suppression>40dBc
- Noise Floor better than -158dBm/Hz
- Single 5V Power Supply

#### Ordering Information

RF2850 **Direct Quadrature Modulator** RF2850 PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc. 7628 Thorndike Road Greensboro, NC 27409, USA

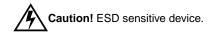
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### **RF2850**

**Absolute Maximum Ratings** 

Parameter	Rating	Unit				
Supply Voltage	-0.5 to +5.3	V				
LO Input	+10	dBm				
Operating Temperature	-40 to +85	°C				
Storage Temperature	-65 to +150	°C				



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Parameter	Specification		Unit	Condition		
	Min.	Тур.	Max.		Condition	
High Band Performance	High Band Performance (1900MHz) with CW Baseband Inputs					
LO Input Port						
LO Drive Level		-5		dBm		
LO Input Impedance		50		Ω		
LO Port Return Loss		13		dB		
Modulation Input						
Frequency Range	DC		250	MHz		
Reference Voltage		2.05		V	Baseband common mode voltage	
Baseband Input Level		0.25		$V_{P-P}$	0.25V <sub>P-P</sub> per pin, 500 mV V <sub>P-P</sub> differential,	
					I/Q in quadrature	
I/Q Signal		200		kHz	CW baseband signal	
Input Impedance		40		kΩ	Measured at DC	
Bandwidth (-1 dB)		130		MHz	500 mV V <sub>P-P</sub> differential, I/Q at 2.05 V DC	
Input Bias Current			40	μΑ		
I/Q Modulator Output						
RF Frequency Range	1700		2500	MHz	T=25°C, V <sub>CC</sub> =5V	
RF Output Power		-6		dBm		
RF Output Return Loss		15		dB		
RF Output P1dB	4	5		dBm		
Carrier Suppression	20	25		dBc	Unadjusted (see note)	
Carrier Suppression	35	55		dBc	Adjusted. T=-40°C to +85°C	
Sideband Suppression	30	45		dBc	Unadjusted	
IM3 Suppression		52		dBc	Two tone baseband input @ 500 mV <sub>P-P</sub> dif-	
					ferential per tone	
Output IP3	15	20		dBm		
Broadband Noise Floor		-158	-156	dBm/Hz	20MHz offset from LO, all IQ input at bias of 2.05 V	
DC Parameters						
Supply Voltage		5.0		V	Specification	
_	4.75		5.25	V	Operating limits	
Supply Current		60	ble for differ	mA		

Note: 20dBc limit for unadjusted carrier suppression is applicable for differential I and Q inputs only.

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## RF2850

Parameter	Specification		Unit	Condition		
Farameter	Min.	Тур.	Max.	Offic	Condition	
High Band Performance with PCS CDMA and W-CDMA Baseband Inputs						
W-CDMA 3GPP						
Channel Power		-13		dBm	3.84MHz integrated bandwidth, ESG-D with LPF	
ACPR @ 1960MHz		-68	-62	dBc		
SNR @ 1960MHz		-74	-70	dBc		
ACPR @ 2140MHz		-65	-62	dBc		
SNR @ 2140MHz		-74	-70	dBc		
Noise Floor @ 20MHz Offset		-156	-155	dBm/Hz	20MHz offset from LO	
PCS CDMA						
Channel Power		-13		dBm	1.2288MHz integrated bandwidth	
ACPR @ 1960MHz		-72	-70	dBc	30 kHz integrated bandwidth	
W-CDMA 1 MHz BW						
Channel Power		-14		dBm	1 MHz integrated bandwidth at adjacent channel	
ACPR @ 2140MHz		-74	-71	dBc		
SNR @ 2140MHz		-85	-82	dBc		
Noise Floor @ 20MHz Offset		-157	-156	dBm/Hz	20MHz offset from LO	

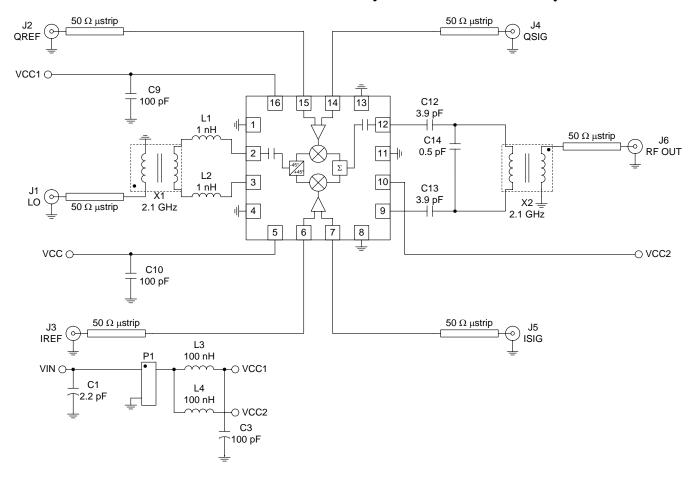
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### RF2850

Pin	Function	Description	Interface Schematic
1	GND	Ground connection.	
2	LO	LO input signal. This pin has an internal DC-blocking capacitor. This port is voltage-driven so matching at different frequencies is generally not required.	ro o
3	LOREF The reference end of local oscillator.		
4	GROD Ground connection.		
5	VCC	Power supply. An external capacitor is required.	
6	I REF	Reference voltage for the I mixer. The DC voltage should be the same as the DC supplied to I SIG (pin 7). See pin 7 for more information.	V <sub>CC</sub>
		The SIG and REF inputs are inputs of a differential amplifier. Therefore, the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, the Q SIG and Q REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a differential mode which will increase gain.	2 pF =
7	I SIG	Baseband input to the I mixer. This pin is DC-coupled. The input drive level determines output power and linearity performance. For better carrier/sideband suppression and dynamic range, the drive level should be as high as possible to meet the required linearity performance. The recommended DC level for this pin is 2.05 V.	2 pF =
8	GND	Ground connection.	
9	RFREF	The reference end of RF input.	
10	VCC	Power supply. An external capacitor is required.	
11	GND	Ground connection.	
12	RF OUT	RF Output. This pin has an internal DC-blocking capacitor. At some frequencies, external matching may be needed to optimize output power.	→ CRF OUT
13	GND	Ground connection.	
14	Q SIG	Baseband input to the Q mixer. This pin is DC-coupled. The input drive level determines the output power and linearity performance. For better carrier/sideband suppression and dynamic range, the drive level should be as high as possible to meet the required linearity performance. The recommended DC level for this pin is 2.05 V.	2 pF =
15	Q REF	Reference voltage for the Q mixer. See pin 14 for more information.	2 pF =
16	VCC	Power supply. An external capacitor is required.	
Pkg Base	GND	Ground connection.	

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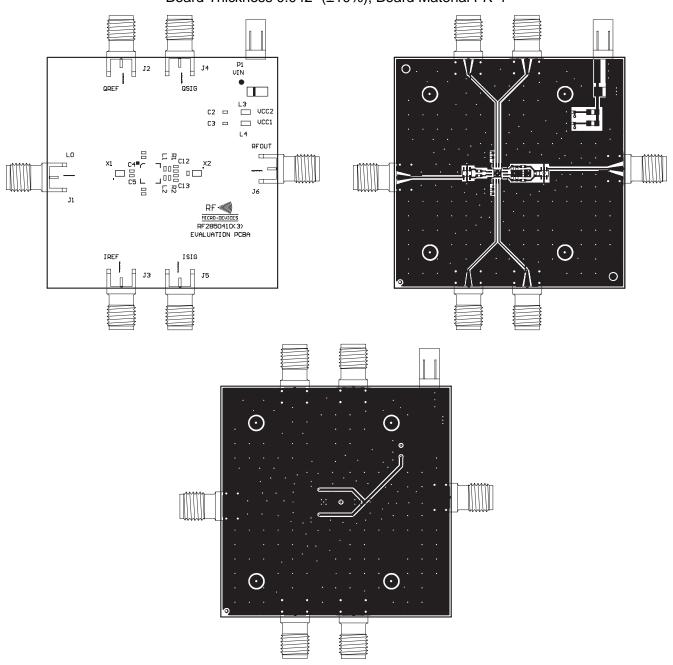
### **Evaluation Board Schematic** 1700MHz to 2500MHz (Differential Drive)



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# **Evaluation Board Layout Board Size 2.00" x 2.00"**

Board Thickness 0.042" (±10%), Board Material FR-4



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